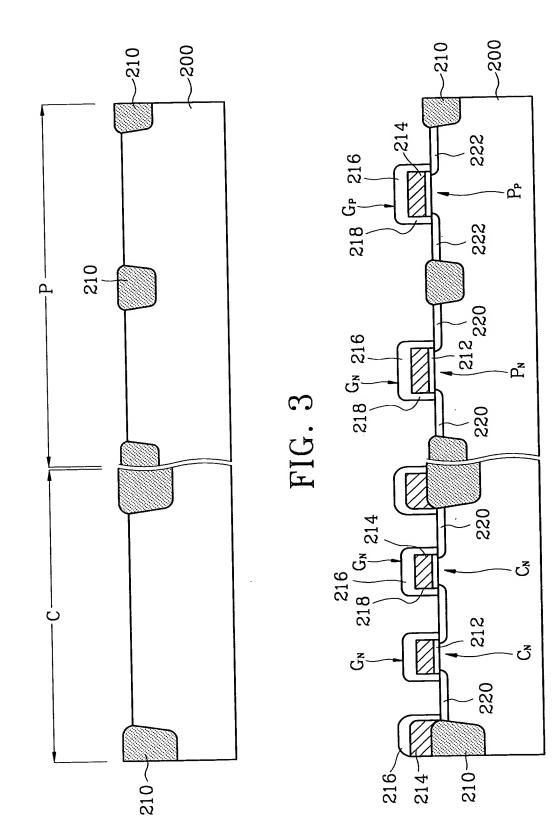
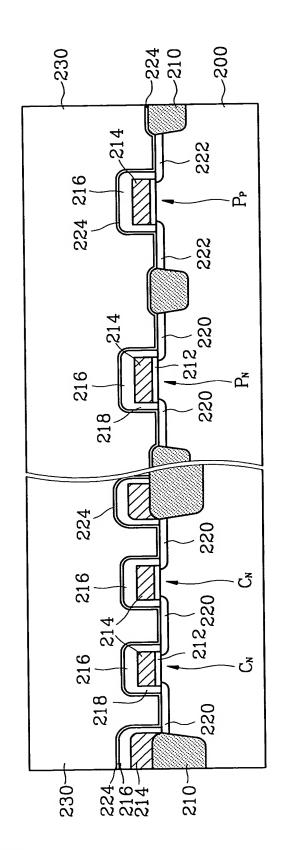


FIG. 2



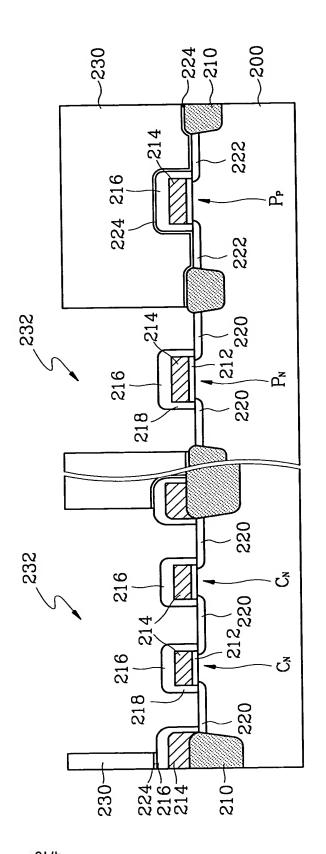
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FIG. 4



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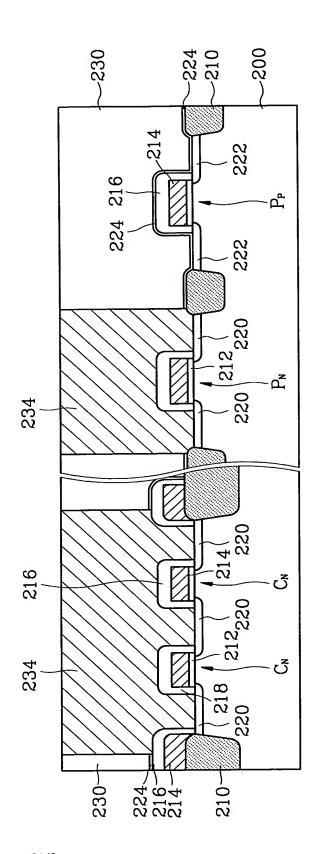
FIG. 5



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FIG. 6



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WETHOD OF FORMING SEMICONDUCTOR DEVICE HAVING CONTACT PAD ON SOURCE/DRAIN REGION IN PERIPHERAL CIRCUIT

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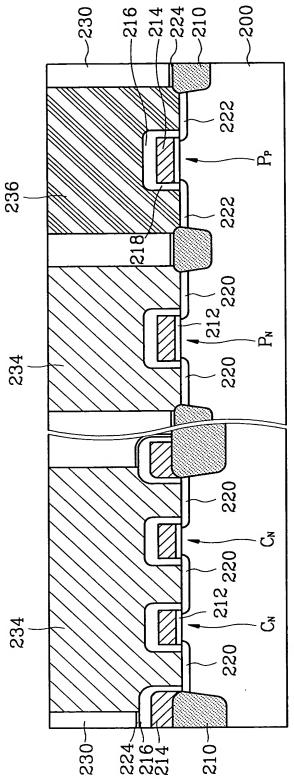


FIG. 8

-230 -224 -210 7200 250 216 | 222 218 ሲ 222 250 (212 / 220 240 240 220 216 214 Č 1212220 218 Č 220 240 210-

91/2

222 -320 -ф 222 | 252 | 250 330 (212 ) 320~ 220 \ 240 220 340 320 Č 212 220 330 Č \ 220 \ 240 340 210-232 224 216-214-

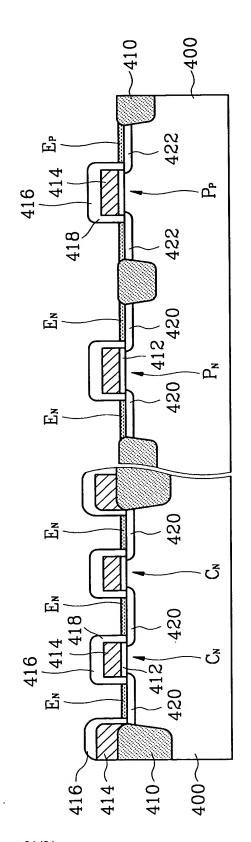
\_232 \_230 \_224 \_210

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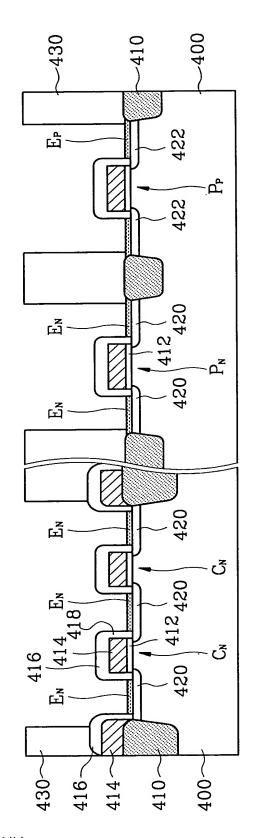
.232 .230 -224 .210 ~310 .360 -320 Ъ 222 1 330 320→ -340, 340 330 \ 220 \ 240 216-214-210-91/6

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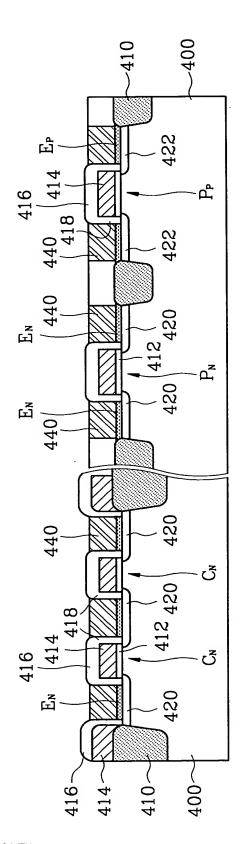
FIG. 11



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FIG. 14A

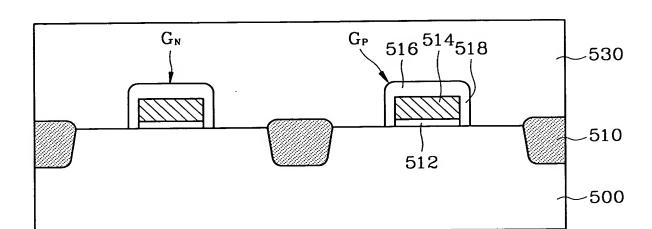
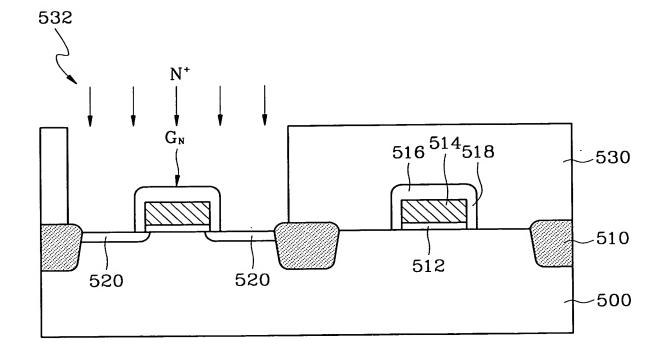


FIG. 14B



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FIG. 14C

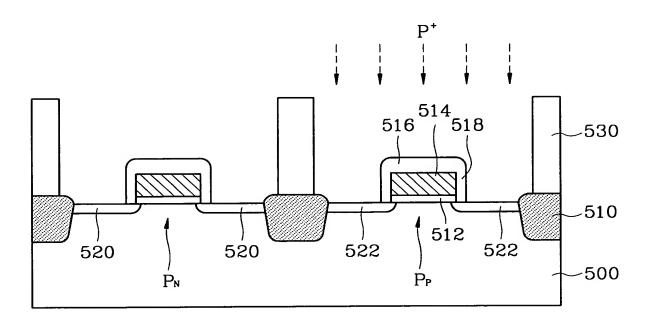
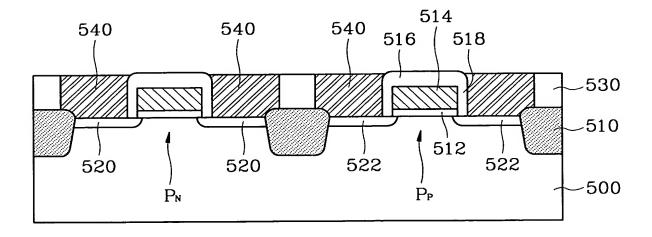


FIG. 14D



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## FIG. 15A

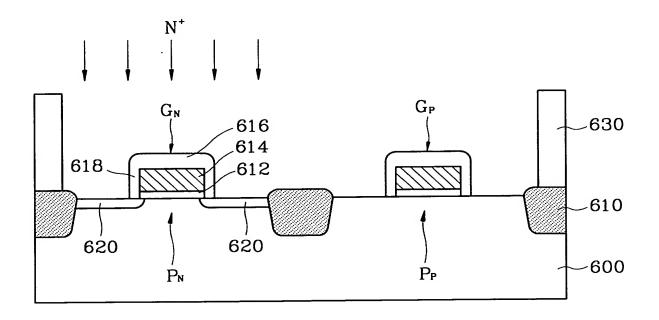
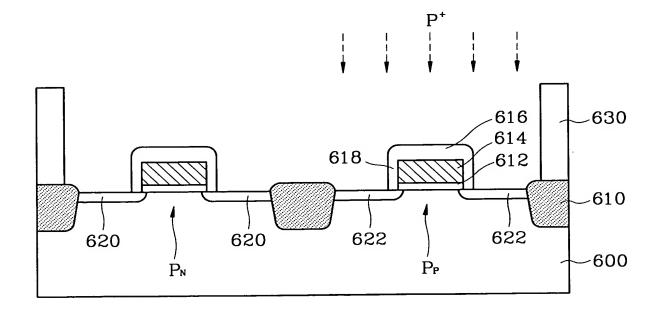


FIG. 15B



16/16°<sub>v.</sub>,

FIG. 15C

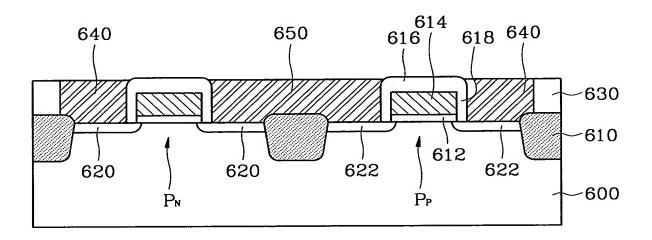


FIG. 16 (PRIOR ART)

